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# **BUK9K89-100E**

## **Dual N-channel TrenchMOS logic level FET**

23 April 2013

**Product data sheet** 

### 1. General description

Dual logic level N-channel MOSFET in a LFPAK56D package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

#### 2. Features and benefits

- Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with V<sub>GS(th)</sub> > 0.5 V @ 175 °C

## 3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Start-stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

#### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V <sub>DS</sub>	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	-	100	V	
I <sub>D</sub>	drain current	V <sub>GS</sub> = 5 V; T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	12.5	Α	
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	-	38	W	
Static characte	Static characteristics FET1 and FET2							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 12$		-	75.8	89	mΩ	
Dynamic chara	Dynamic characteristics FET1 and FET2							
$Q_{GD}$	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ °C}; Fig. 14; Fig. 15$		-	4.2	-	nC	



## 5. Pinning information

**Table 2.** Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1	1	
3	S2	source2		
4	G2	gate2		
5	D2	drain2		
6	D2	drain2	_	mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1	21.7.1.1005 (0011200)	

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BUK9K89-100E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

## 7. Marking

Table 4. Marking codes

Type number	Marking code
BUK9K89-100E	98910E

# 8. Limiting values

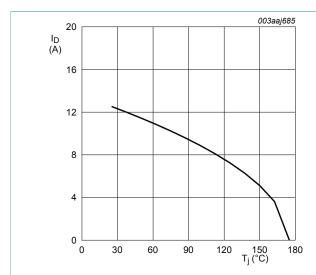
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> ≥ 25 °C; T <sub>j</sub> ≤ 175 °C		-	100	V
$V_{DGR}$	drain-gate voltage	$R_{GS}$ = 20 kΩ; $T_j \ge 25$ °C; $T_j \le 175$ °C		-	100	V
$V_{GS}$	gate-source voltage	T <sub>j</sub> ≤ 175 °C; DC		-10	10	V
		T <sub>j</sub> ≤ 175 °C; Pulsed	[1][2]	-15	15	V
I <sub>D</sub>	drain current	T <sub>mb</sub> = 25 °C; V <sub>GS</sub> = 5 V; <u>Fig. 1</u>		-	12.5	Α
		T <sub>mb</sub> = 100 °C; V <sub>GS</sub> = 5 V; <u>Fig. 1</u>		-	8.9	Α
I <sub>DM</sub>	peak drain current	$T_{mb}$ = 25 °C; pulsed; $t_p \le 10 \mu s$ ; Fig. 4		-	50	Α

Symbol	Parameter	Conditions		Min	Max	Unit
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>		-	38	W
T <sub>stg</sub>	storage temperature			-55	175	°C
T <sub>j</sub>	junction temperature			-55	175	°C
T <sub>sld(M)</sub>	peak soldering temperature			-	260	°C
Source-drai	n diode FET1 and FET2		'			
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C		-	12.5	Α
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	50	Α
Avalanche F	Ruggedness FET1 and FET2					_
E <sub>DS(AL)S</sub>	non-repetitive drain-source avalanche energy	$I_D$ = 12.5 A; $V_{sup} \le 100 \text{ V}$ ; $V_{GS}$ = 5 V; $T_{j(init)}$ = 25 °C; Fig. 3	[3][4]	-	21	mJ

- Accumulated Pulse duration up to 50 hours delivers zero defect ppm
- Significantly longer life times are achieved by lowering  $T_i$  and or  $V_{GS}$ . [2]
- Refer to application note AN10273 for further information
- [3] [4] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



Continuous drain current as a function of mounting base temperature

$$V_{GS} \ge 5V$$

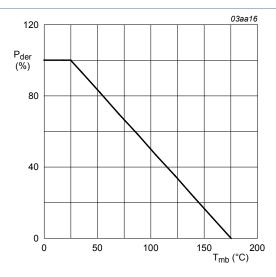


Fig. 2. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

**Dual N-channel TrenchMOS logic level FET** 

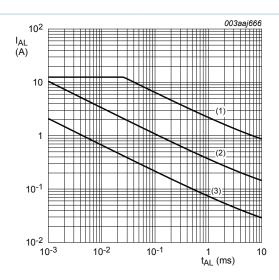


Fig. 3. Single-pulse and repetitive avalanche rating; avalanche current as a function of avalanche time, FET1 and FET2

- (1) Single-pulse;  $T_j = 25 \,^{\circ}C$ .
- (2) Single-pulse;  $T_j = 150 \,^{\circ}C$ .
  - (3) Repetitive.

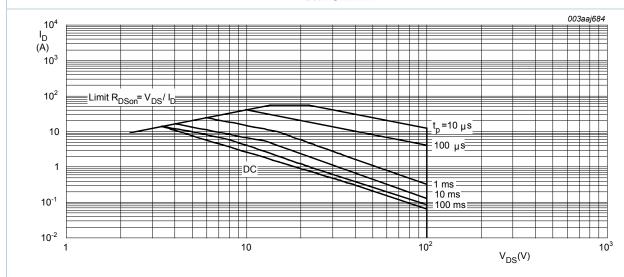


Fig. 4. Safe operating area; continuous and peak drain current as a function of drain-source voltage

$$T_{mb} = 25 \,^{\circ}C; I_{DM}$$
 is single pulse

#### 9. Thermal characteristics

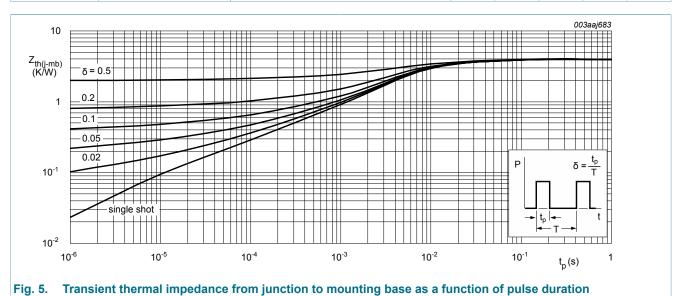
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(i-mb)</sub>	thermal resistance	Fig. 5	-	-	3.96	K/W
,	from junction to					
	mounting base					

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Minimum footprint; mounted on a printed circuit board	-	95	-	K/W



### 10. Characteristics

Table 7. Characteristics

	Conditions	Min	Тур	Max	Unit
cteristics FET1 and FET2		'			
drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	90	-	-	V
breakdown voltage	$I_D$ = 250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	100	-	-	V
gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	1.4	1.7	2.1	V
	I <sub>D</sub> = 1 mA; V <sub>DS</sub> = V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; Fig. 10; Fig. 11	0.5	-	-	V
	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 10; Fig. 11	-	-	2.45	V
drain leakage current	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.02	1	μA
	V <sub>DS</sub> = 100 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	-	500	μΑ
gate leakage current	V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
	V <sub>GS</sub> = 10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
drain-source on-state	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	75.8	89	mΩ
resistance	V <sub>GS</sub> = 5 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 175 °C; Fig. 12; Fig. 13	-	205.4	245	mΩ
	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 12</u>	-	74.9	85	mΩ
	drain-source breakdown voltage  gate-source threshold voltage  drain leakage current  gate leakage current	$ \begin{array}{l} \text{drain-source} \\ \text{breakdown voltage} \end{array} \qquad \begin{array}{l} I_D = 250 \; \mu \text{A}; \; V_{GS} = 0 \; \text{V}; \; T_j = -55 \; ^{\circ}\text{C} \\ \\ I_D = 250 \; \mu \text{A}; \; V_{GS} = 0 \; \text{V}; \; T_j = 25 \; ^{\circ}\text{C} \\ \end{array} $ $ \begin{array}{l} \text{gate-source threshold} \\ \text{voltage} \end{array} \qquad \begin{array}{l} I_D = 1 \; \text{mA}; \; V_{DS} = V_{GS}; \; T_j = 25 \; ^{\circ}\text{C}; \\ \hline \text{Fig. 10}; \; \hline \text{Fig. 11} \\ \hline \\ I_D = 1 \; \text{mA}; \; V_{DS} = V_{GS}; \; T_j = 175 \; ^{\circ}\text{C}; \\ \hline \text{Fig. 10}; \; \hline \text{Fig. 11} \\ \hline \\ I_D = 1 \; \text{mA}; \; V_{DS} = V_{GS}; \; T_j = -55 \; ^{\circ}\text{C}; \\ \hline \text{Fig. 10}; \; \hline \text{Fig. 11} \\ \hline \\ \text{drain leakage current} \end{array} \qquad \begin{array}{l} V_{DS} = 100 \; \text{V}; \; V_{GS} = 0 \; \text{V}; \; T_j = 25 \; ^{\circ}\text{C} \\ \hline V_{DS} = 100 \; \text{V}; \; V_{GS} = 0 \; \text{V}; \; T_j = 175 \; ^{\circ}\text{C} \\ \hline V_{GS} = -10 \; \text{V}; \; V_{DS} = 0 \; \text{V}; \; T_j = 25 \; ^{\circ}\text{C} \\ \hline V_{GS} = 10 \; \text{V}; \; V_{DS} = 0 \; \text{V}; \; T_j = 25 \; ^{\circ}\text{C} \\ \hline V_{GS} = 5 \; \text{V}; \; I_D = 5 \; \text{A}; \; T_j = 25 \; ^{\circ}\text{C}; \; \overline{\text{Fig. 12}} \\ \hline V_{GS} = 5 \; \text{V}; \; I_D = 5 \; \text{A}; \; T_j = 175 \; ^{\circ}\text{C}; \\ \hline Fig. 12; \; \overline{\text{Fig. 13}} \end{array} \qquad \begin{array}{l} I_D = 250 \; \text{C}; \; F_{DS} = 1200 \; \text{V}; \; V_{DS} = 100 \;$	$ \begin{array}{llllllllllllllllllllllllllllllllllll$	$\begin{array}{llllllllllllllllllllllllllllllllllll$	$ \begin{array}{c} \text{drain-source} \\ \text{breakdown voltage} \\ \end{array} \begin{array}{c} I_D = 250 \; \mu \text{A; V}_{GS} = 0 \; \text{V; T}_j = -55 \; ^{\circ}\text{C} \\ \\ I_D = 250 \; \mu \text{A; V}_{GS} = 0 \; \text{V; T}_j = 25 \; ^{\circ}\text{C} \\ \end{array} \begin{array}{c} 100  -  -  \\ \\ \\ 100  -  -  \\ \\ \\ 100  -  -  \\ \\ \\ 100  -  -  \\ \\ \\ 100  -  -  \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Dynamic cl	haracteristics FET1 and FE	T2				
Q <sub>G(tot)</sub>	total gate charge	I <sub>D</sub> = 5 A; V <sub>DS</sub> = 80 V; V <sub>GS</sub> = 10 V;	-	16.8	-	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	1.7	-	nC
$Q_{GD}$	gate-drain charge		-	4.2	-	nC
C <sub>iss</sub>	input capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 25 V; f = 1 MHz;	-	831	1108	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 16</u>	-	81	97	pF
C <sub>rss</sub>	reverse transfer capacitance		-	59	81	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = 80 V; $R_{L}$ = 16 $\Omega$ ; $V_{GS}$ = 10 V;	-	3.6	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 10 \Omega; T_j = 25 °C; I_D = 5 A$	-	5.8	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	22.1	-	ns
t <sub>f</sub>	fall time		-	12.1	-	ns
Source-dra	nin diode FET1 and FET2	1	1	1	1	
V <sub>SD</sub>	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 17$	-	0.78	1.2	V
t <sub>rr</sub>	reverse recovery time	$I_S = 5 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$	-	29.9	-	ns
Q <sub>r</sub>	recovered charge	$V_{DS} = 50 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	39.9	-	nC

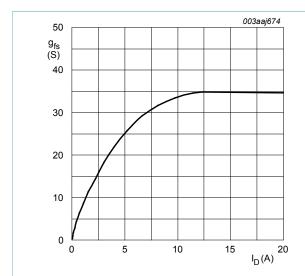


Fig. 6. Forward transconductance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C; V_{DS} = 15 \, V$$

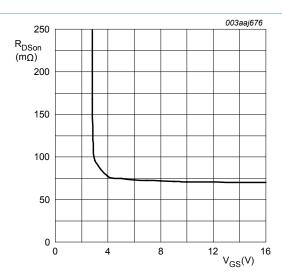


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25 \,^{\circ}C; \ I_D = 5 A$$

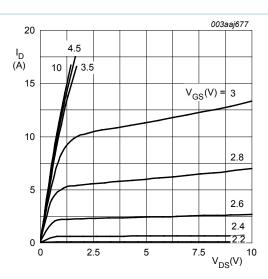


Fig. 8. Output characteristics: drain current as a function of drain-source voltage; typical values



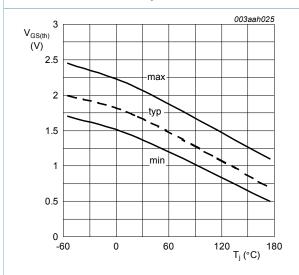


Fig. 10. Gate-source threshold voltage as a function of junction temperature

$$I_D = 1 \text{ mA}; \ V_{DS} = V_{GS}$$

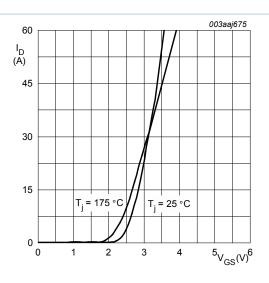


Fig. 9. Transfer characteristics: drain current as a function of gate-source voltage; typical values

$$V_{DS} = 10V$$

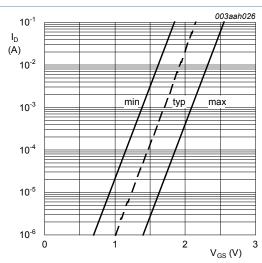


Fig. 11. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25$$
°C;  $V_{DS} = 5V$ 

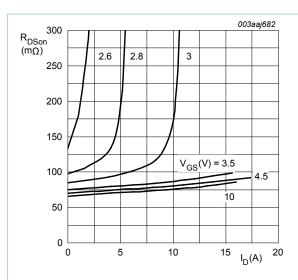


Fig. 12. Drain-source on-state resistance as a function of drain current; typical values

$$T_j = 25 \,^{\circ}C$$

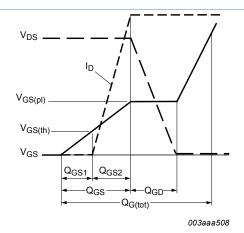


Fig. 14. Gate charge waveform definitions

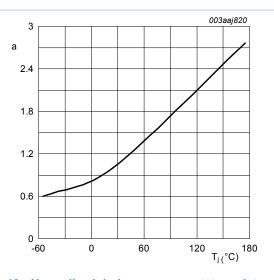


Fig. 13. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon (25^{\circ}C)}}$$

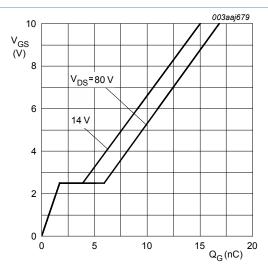


Fig. 15. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25 \,^{\circ}C; I_D = 5A$$

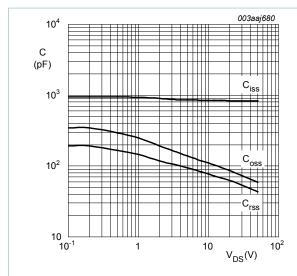
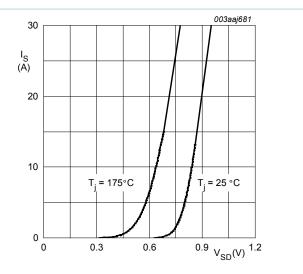


Fig. 16. Input, output and reverse transfer capacitances | Fig. 17. Source current as a function of source-drain as a function of drain-source voltage; typical values

$$V_{GS} = 0 V; f = 1MHz$$



voltage; typical values

$$V_{GS} = 0 V$$

### 11. Package outline

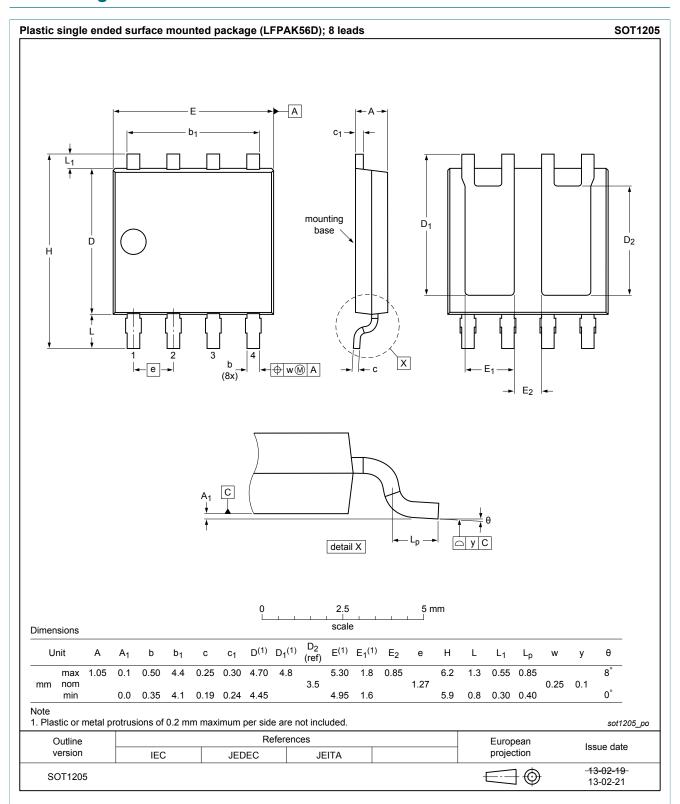


Fig. 18. Package outline LFPAK56D (SOT1205)

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#### **Dual N-channel TrenchMOS logic level FET**

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Product [short] data sheet	Production	This document contains the product specification.

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Nexperia

## **BUK9K89-100E**

#### **Dual N-channel TrenchMOS logic level FET**

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